

ETHANOL VAPOR INFLUENCE ON ELECTRICAL PROPERTIES OF POROUS SiC

Freestanding porous silicon carbide (PSiC) was synthesized via electrochemical etching of silicon carbide (3C-SiC). The surface morphology of PSiC has been studied using scanning electron microscopy (SEM). The electrical properties of porous SiC structures were investigated using impedance measurements in dry air and in saturated vapor of ethanol.

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